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RLT1300-30G

TECHNICAL DATA



High Power Infrared Laserdiode

Structure: **GaInAsP/InP SQW structure**

Lasing wavelength: **single mode 1300 nm typ.**

Typ. optical power: **30 mW**

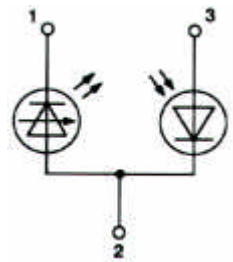
Package: **9 mm (SOT-148)**

NOTE!

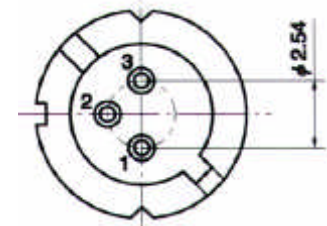
LASERDIODE
MUST BE COOLED!



PIN CONNECTION:



- 1) Laser diode cathode
- 2) Laser diode anode and photodiode cathode
- 3) Photodiode anode



Absolute Maximum Ratings (Tc=25°C)

CHARACTERISTIC	SYMBOL	RATING	UNIT
Maximum LD current	I_f	200	mA
Optical Output Power	P_o	40	mW
LD Reverse Voltage	$V_{R(LD)}$	1.5	V
PD Reverse Voltage	$V_{R(PD)}$	6	V
Operating Temperature	T_c	-20 .. +40	°C
Storage Temperature	T_{STG}	-40 .. +85	°C

Optical-Electrical Characteristics (Tc = 25°C)

CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN	TYP	MAX	UNIT
Aperture	A	cw		1 x 5		μm^2
Optical Output Power	P_o	cw		30	40	mW
Threshold Current	I_{th}	cw		40		mA
Operation Current	I_{op}	$P_o = 30 \text{ mW}$		160		mA
Forward Voltage	U_f	$P_o = 30 \text{ mW}$		2		V
Lasing Wavelength	λ_p	$P_o = 30 \text{ mW}$	1270	1300	1330	nm
Beam Divergence	$\theta_{//}$	$P_o = 30 \text{ mW}$		25		°
Beam Divergence	$\theta_{\perp}$	$P_o = 30 \text{ mW}$		40		°
Monitor Current	I_m	$P_o = 30 \text{ mW}$	> 20	500	1500	μA